

U.S.S.N. 10,769,245

Claim Amendments

Please amend claim 28 as follows:

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Listing of Claims

1. (previously presented) A method of cleaning a wafer surface, comprising the steps of:

providing a wafer surface comprising at least one of a metal and a dielectric layer;

providing a surfactant composition solution;

subjecting said wafer surface to a plurality of polishing steps;

applying said surfactant composition solution to said wafer surface after at least one of said plurality of polishing steps to render said wafer surface hydrophilic; and

then rinsing said wafer surface.

2. (previously presented) The method of claim 1 wherein said applying said surfactant composition solution comprises applying said surfactant composition after completion of said plurality of

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polishing steps.

3. (previously presented) The method of claim 1 wherein said surfactant composition solution comprises an aqueous alcohol solution.

4. cancelled

5. (previously presented) The method of claim 1 wherein said rinsing said wafer surface comprises providing deionized water and rinsing said wafer using said deionized water.

6. cancelled

7. cancelled

8. (original) The method of claim 3 wherein said aqueous alcohol solution comprises from about 0.01% to about 1% alcohol by volume.

9. cancelled

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10. cancelled

11. (previously presented) The method of claim 3 wherein said alcohol comprises octanol:

12. (previously presented) The method of claim 3 further comprising ethylene oxide in said aqueous alcohol solution.

13. (previously presented) A method of cleaning a hydrophobic wafer surface, comprising the steps of:

providing a wafer surface comprising at least one of a metal and a dielectric layer;

providing a surfactant composition solution comprising an aqueous alcohol solution;

subjecting said wafer surface to a plurality of polishing steps;

applying said surfactant composition solution to said wafer surface after each of said plurality of polishing steps to

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form a hydrophilic surface; and

rinsing said wafer surface with water.

14. cancelled

15. (previously presented) The method of claim 13 wherein said surfactant composition solution comprises from about 0.01% to about 1% alcohol by volume.

16. (previously presented) The method of claim 13 further comprising ethylene oxide in said surfactant composition solution.

Claims 17- 20 cancelled

21. (previously presented) The method of claim 1, wherein the steps of applying said surfactant composition solution and rinsing are carried out after each of said plurality of polishing steps.

22. (previously presented) The method of claim 1, wherein said

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plurality of polishing steps comprises a copper polishing step.

23. (previously presented) The method of claim 1, said plurality of polishing steps comprises an oxide polishing step.

24. (previously presented) The method of claim 1, wherein said plurality of polishing steps comprises a low-K oxide polishing step.

25. (previously presented) The method of claim 1, wherein said plurality of polishing steps comprises a metal nitride polishing step.

26. (previously presented) The method of claim 1, wherein said surfactant composition solution comprises an alcohol having the formula $C_nH_{2n-1}OH$, where n is any one of the integers 4-12.

27. (previously presented) The method of claim 13, wherein said plurality of polishing steps comprises a copper polishing step.

28. (currently amended) The method of claim 13, wherein said plurality of polishing steps comprises an oxide polishing step.

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29. (previously presented) The method of claim 13, wherein said plurality of polishing steps comprises a low-K oxide polishing step.

30. (previously presented) The method of claim 13, wherein said plurality of polishing steps comprises a metal nitride polishing step.